



PNP Transistor Bare Die, 2N3637

Rev 1.0
31/01/25

General purpose high voltage amplifier in bare die form
Complement to NPN 2N3501

Features:

- High Breakdown Voltage
- Low $V_{CE(sat)}$
- Characterized at temperature extremes
- High Reliability Gold Back Metal
- High Reliability tested grades for Military + Space

Ordering Information:

The following part suffixes apply:

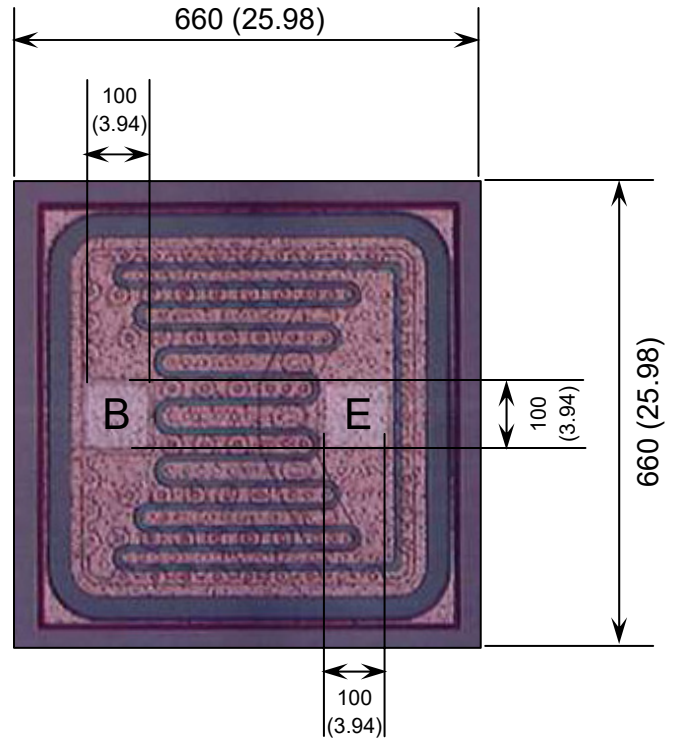
- No suffix - MIL-STD-750 /2072 Visual Inspection
- "H" - MIL-STD-750 /2072 Visual Inspection
+ MIL-STD-38534 Class H LAT
- "K" - MIL-STD-750 /2072 Visual Inspection
+ MIL-STD-38534 Class K LAT

LAT = Lot Acceptance Test.

For further information on LAT process flows see below.

www.siliconsupplies.com/quality/bare-die-lot-qualification

Die Dimensions in μm (mils)



E = EMITTER B = BASE

DIE BACK = COLLECTOR

Supply Formats:

- Default – Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape – Specific request
- Unsawn Wafer – Specific request
- With additional electrical selection – Specific request
- Sawn as pairs or adjacent pair pick – Specific request

Mechanical Specification

Die Size (Excluding Saw Street)	660 x 660 25.98 x 25.98	μm mils
Base & Emitter Pad Size	100 x 100 3.94 x 3.94	μm mils
Die Thickness	230 (± 20) 9.06 (± 0.79)	μm mils
Top Metal Composition	Al - 2.6 μm	
Back Metal Composition	AuAs - 0.9 μm	





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Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-175	V
Collector-Emitter Voltage	V_{CEO}	-175	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1	A
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}$	-175	-	-	V
Collector-Emitter Breakdown Voltage ¹	$V_{(BR)CEO}$	$I_C = -10\text{mA}$	-175	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -100\text{V}$	-	-	-100	nA
		$V_{CB} = -175\text{V}$	-	-	-10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -3\text{V}$	-	-	-50	nA
		$V_{EB} = -5\text{V}$	-	-	-10	μA
ON CHARACTERISTICS¹						
Forward-Current Transfer Ratio	h_{FE}	$V_{CE} = -10\text{V}, I_C = -0.1\text{mA}$	55	-	-	-
		$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	90	-	-	-
		$V_{CE} = -10\text{V}, I_C = -10\text{mA}$	100	-	-	-
		$V_{CE} = -10\text{V}, I_C = -50\text{mA}$	100	-	300	-
		$V_{CE} = -10\text{V}, I_C = -150\text{mA}$	60	-	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$	-	-	-0.3	V
		$I_C = -50\text{mA}, I_B = -5\text{mA}$	-	-	-0.6	V
Base Saturation Voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$	-	-	-0.8	V
		$I_C = -50\text{mA}, I_B = -5\text{mA}$	-0.65	-	-0.9	V
SMALL SIGNAL CHARACTERISTICS²						
Forward Current Transfer Ratio	$ h_{fe} $	$V_{CE} = -30\text{V}, I_C = -30\text{mA}, f = 100\text{MHz}$	2.0	-	8.5	-
Forward Current Transfer Ratio	h_{fe}	$V_{CE} = -10\text{V}, I_C = -10\text{mA}, f = 1\text{kHz}$	80	-	320	-
Short-Circuit Input Impedance	h_{ie}	$V_{CE} = -10\text{V}, I_C = -10\text{mA}, f = 1\text{kHz}$	200	-	1200	Ω
Open-Circuit Input Impedance	h_{oe}	$V_{CE} = -10\text{V}, I_C = -10\text{mA}, f = 1\text{kHz}$	-	-	200	μs
Output Capacitance	C_{obo}	$V_{CB} = -20\text{V}, I_E = 0, 100\text{kHz} \leq f \leq 1\text{MHz}$	-	-	10	pF
Input Capacitance	C_{ibo}	$V_{EB} = -1\text{V}, I_C = 0, 100\text{kHz} \leq f \leq 1\text{MHz}$	-	-	75	pF
Noise Figure	NF	$V_{CE} = 10\text{V}, I_C = 0.5\text{mA}, R_g = 1\text{k}\Omega, f = 100\text{Hz}$	-	-	5	dB
		$V_{CE} = 10\text{V}, I_C = 0.5\text{mA}, R_g = 1\text{k}\Omega, 1\text{kHz} \leq f \leq 10\text{kHz}$	-	-	3	dB

1. Pulse Test: pulse width = 300 μs , duty cycle < 2.0% 2. Not production testing in die form, characterized by chip design & package verification.





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